

Features

- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free Available Upon Request By Adding Suffix "-HF"

Maximum Ratings

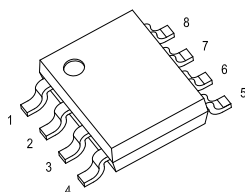
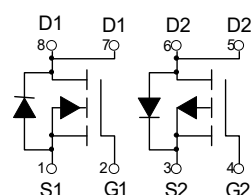
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 62.5°C/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Total Power Dissipation	P_D	2.0	W
N-Channel MOSFET			
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^(Note 1)	$T_A=25^\circ\text{C}$	6.5	A
	$T_A=70^\circ\text{C}$	5.4	A
Pulsed Drain Current ^(Note 2)	I_{DM}	26	A
P-Channel MOSFET			
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^(Note 1)	$T_A=25^\circ\text{C}$	-5.0	A
	$T_A=70^\circ\text{C}$	-4.1	A
Pulsed Drain Current ^(Note 2)	I_{DM}	-20	A

Note: 1. These Tests Are Performed With Infinite Heat Sink.

2. Pulse Width By Max. Junction Temperature.

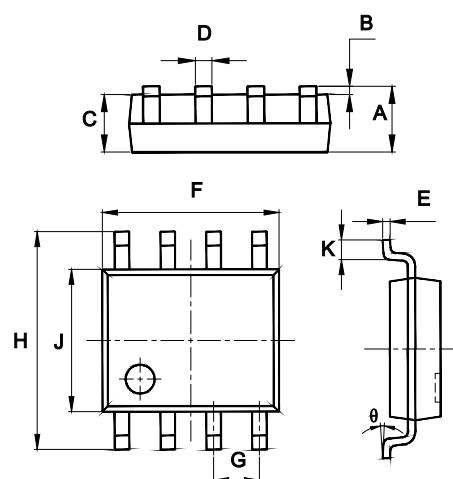
Internal Structure:



Marking: Q4503A

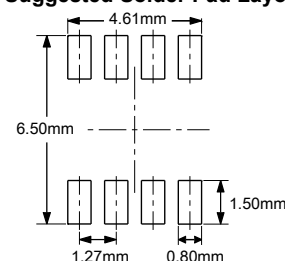
Dual N&P-Channel MOSFET

SOP-8



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.053	0.069	1.35	1.75	
B	0.004	0.010	0.10	0.25	
C	0.053	0.061	1.35	1.55	
D	0.013	0.020	0.33	0.51	
E	0.007	0.010	0.17	0.25	
F	0.185	0.200	4.70	5.10	
G	0.050		1.270		TYP.
H	0.228	0.244	5.80	6.20	
J	0.150	0.157	3.80	4.00	
K	0.016	0.050	0.40	1.27	
θ	0°	8°	0°	8°	

Suggested Solder Pad Layout



N-Channel MOSFET Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.6	2.4	V
Drain-Source On-Resistance ^(Note 3)	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$			30	m Ω
		$V_{GS}=4.5V, I_D=5A$			40	
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=5A$			1.2	V
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	4			S
Dynamic Characteristics						
Input Capacitance ^(Note 4)	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		255		pF
Output Capacitance ^(Note 4)	C_{oss}			45		
Reverse Transfer Capacitance ^(Note 4)	C_{rss}			35		
Total Gate Charge ^(Note 3)	Q_g	$V_{DD}=15V, V_{GS}=10V, I_D=5A$		5.2		nC
Gate-Source Charge ^(Note 4)	Q_{gs}			0.85		
Gate-Drain Charge ^(Note 4)	Q_{gd}			1.3		
Turn-On Delay Time ^(Note 3)	$t_{d(on)}$	$V_{DD}=15V, V_{GS}=10V$ $R_L=2.5\Omega, R_G=3.3\Omega$		4.5		ns
Turn-On Rise Time ^(Note 4)	t_r			2.5		
Turn-Off Delay Time ^(Note 4)	$t_{d(off)}$			14.5		
Turn-Off Fall Time ^(Note 4)	t_f			3.5		

P-Channel Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.6	-2.5	V
Drain-Source On-Resistance ^(Note 3)	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4A$			60	m Ω
		$V_{GS}=-4.5V, I_D=-4A$			90	
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=-5A$			-1.2	V
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-5A$	4			S
Dynamic Characteristics						
Input Capacitance ^(Note 4)	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		520		pF
Output Capacitance ^(Note 4)	C_{oss}			100		
Reverse Transfer Capacitance ^(Note 4)	C_{rss}			65		
Total Gate Charge ^(Note 3)	Q_g	$V_{DD}=-15V, V_{GS}=-10V, I_D=-5A$		9.2		nC
Gate-Source Charge ^(Note 4)	Q_{gs}			1.6		
Gate-Drain Charge ^(Note 4)	Q_{gd}			2.2		
Turn-On Delay Time ^(Note 3)	$t_{d(on)}$	$V_{DD}=-15V, V_{GS}=-10V$ $RL=2.3\Omega, RG=6\Omega$		7.5		ns
Turn-On Rise Time ^(Note 4)	t_r			5.5		
Turn-Off Delay Time ^(Note 4)	$t_{d(off)}$			19		
Turn-Off Fall Time ^(Note 4)	t_f			7		

Note 3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

4. Guaranteed by Design, Not Subject to Production Testing.

N-Channel MOSFET Curve Characteristics

Fig. 1 - Output Characteristics

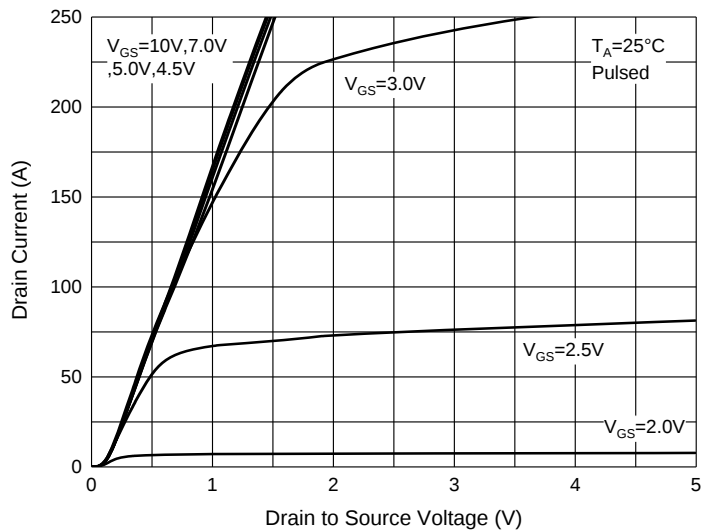


Fig. 2 - Transfer Characteristics

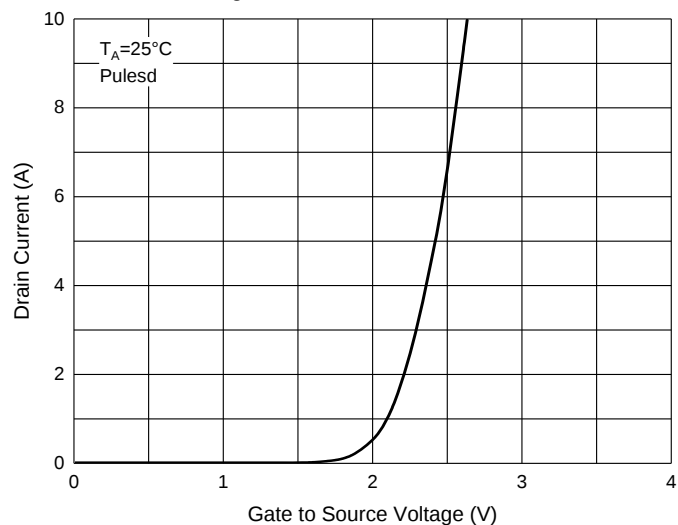


Fig. 3 - $R_{DS(ON)} - I_D$

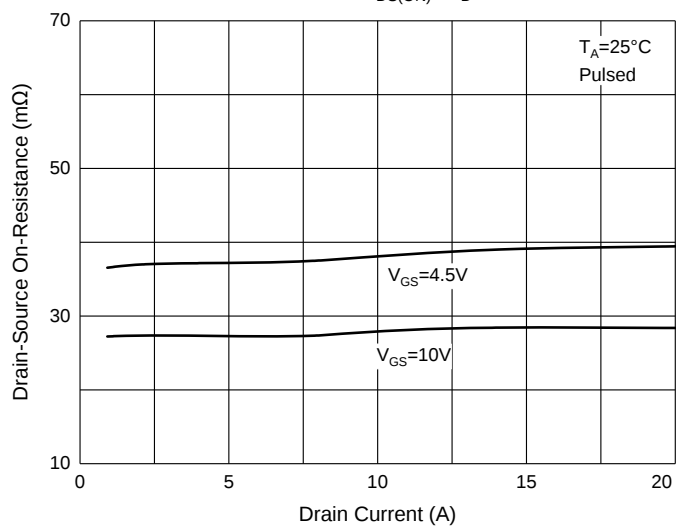


Fig. 4 - $R_{DS(ON)} - V_{GS}$

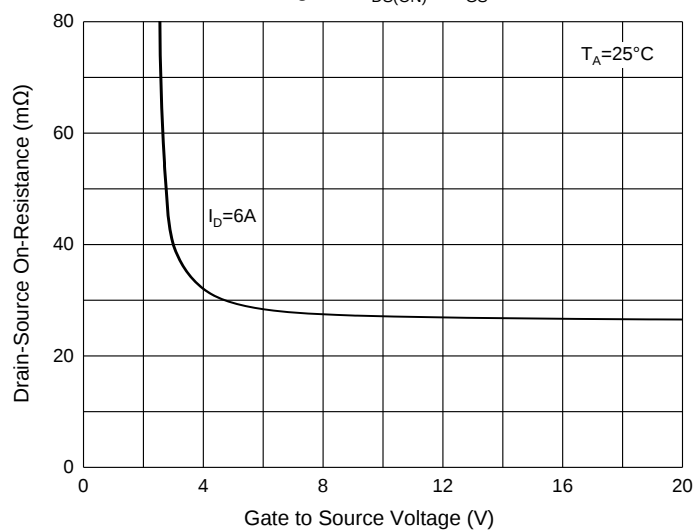
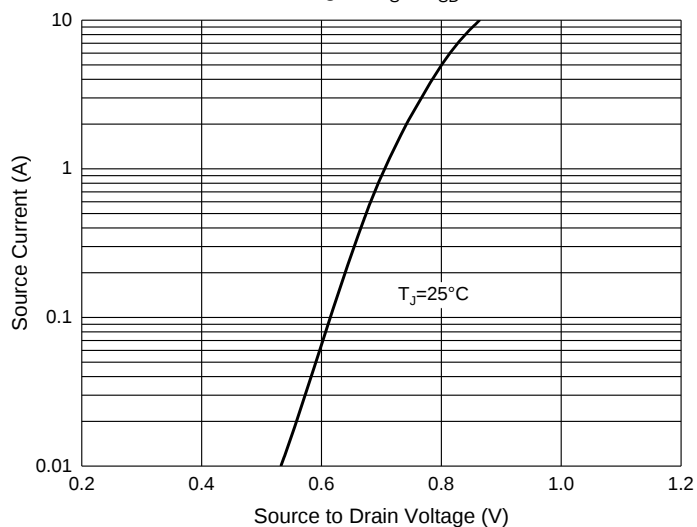


Fig. 5 - $I_S - V_{SD}$



P-Channel MOSFET Curve Characteristics

Fig. 1 - Output Characteristics

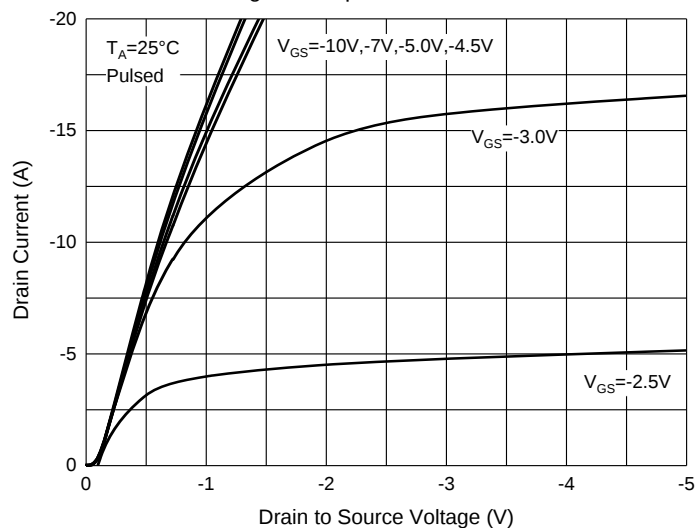


Fig. 2 - Transfer Characteristics

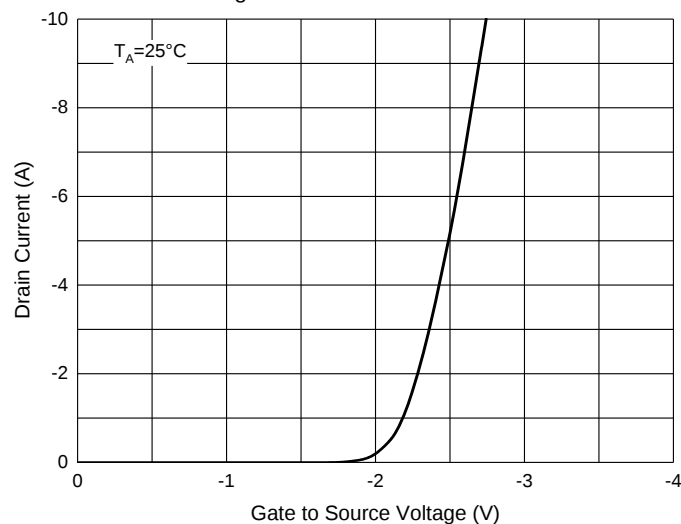


Fig. 3 - $R_{DS(ON)} - I_D$

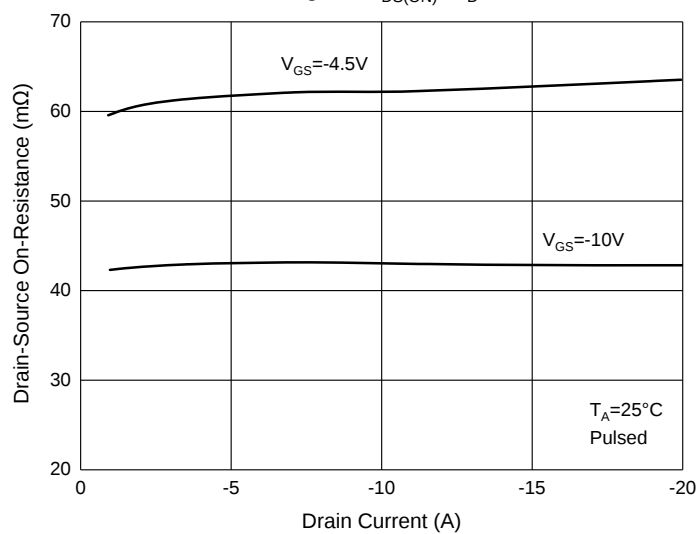


Fig. 4 - $R_{DS(ON)} - V_{GS}$

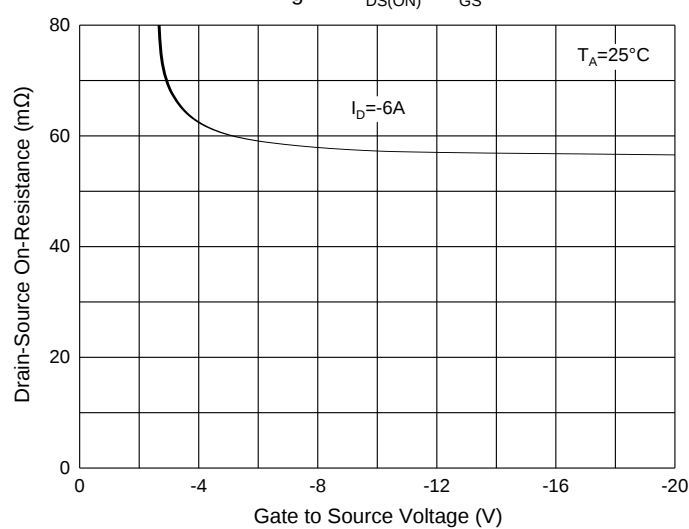
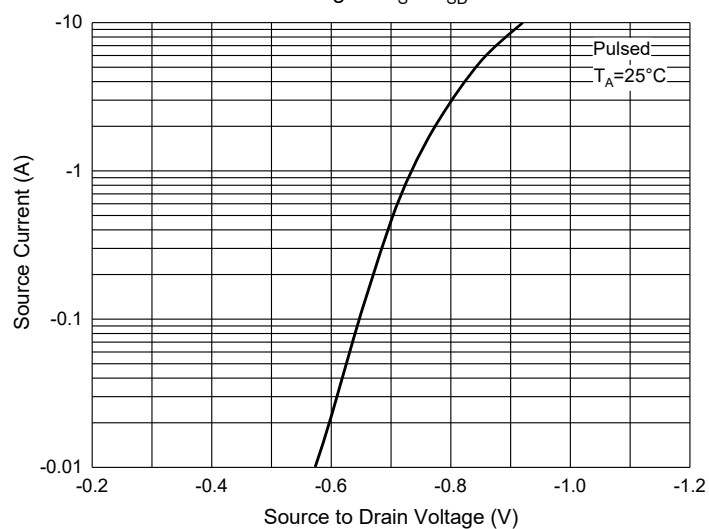


Fig. 5 - $I_S - V_{SD}$



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 4Kpcs/Reel

Note : Adding "-HF" Suffix For Halogen Free, eg. Part Number-TP-HF

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